

### BD233/235/237

# Medium Power Linear and Switching Applications

• Complement to BD 234/236/238 respectively



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Para	meter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	80	V
V <sub>CER</sub>	Collector-Emitter Voltage	: BD233	45	V
		: BD235	60	V
		: BD237	100	V
V <sub>EBO</sub>	Emitter-Base Voltage		5	V
I <sub>C</sub>	Collector Current (DC)		2	Α
I <sub>CP</sub>	*Collector Current (Pulse)		6	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C	:)	25	W
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage					
	: BD233	$I_C = 100 \text{mA}, I_B = 0$	45			V
	: BD235		60			V
	: BD237		80			V
I <sub>CBO</sub>	Collector Cut-off Current					
	: BD233	$V_{CB} = 45V, I_{E} = 0$			100	μΑ
	: BD235	$V_{CB} = 60V, I_{E} = 0$			100	μΑ
	: BD237	$V_{CB} = 100V, I_{E} = 0$			100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 2V, I_{C} = 150 \text{mA}$	40			
		$V_{CE} = 2V, I_{C} = 1A$	25			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.1A$			0.6	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage	$V_{CE} = 2V, I_{C} = 1A$			1.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 250mA$	3			MHz

<sup>\*</sup> Pulse Test: PW=300µs, duty Cycle=1.5% Pulsed

# **Typical Characteristics**

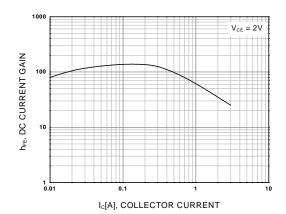


Figure 1. DC current Gain

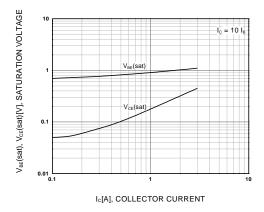


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

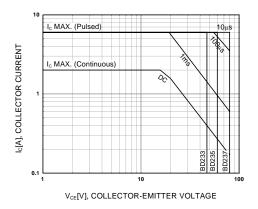


Figure 3. Safe Operating Area

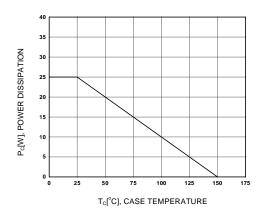
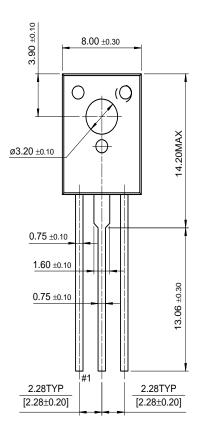


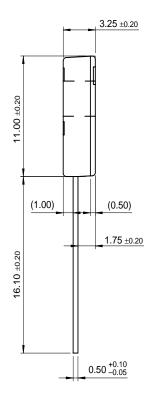
Figure 4. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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